

NXP BTA140-800 4Q Triac datasheet

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Planar passivated four quadrant triac in a SOT78 (T0-220AB) plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance.

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BTA140-800

4Q Triac

12 November 2013

Product data sheet

1. General description

Planar passivated four quadrant triac in a SOT78 (T0-220AB) plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance.

2. Features and benefits

- High blocking voltage capability
- High noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants

3. Applications

- General purpose motor controls
- General purpose switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	800	V
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	-	190	A
$I_{T(\text{RMS})}$	RMS on-state current	full sine wave; $T_{mb} \leq 91\text{ }^{\circ}\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	25	A
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ }^{\circ}\text{C}$; Fig. 7	-	6	35	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ }^{\circ}\text{C}$; Fig. 7	-	10	35	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ }^{\circ}\text{C}$; Fig. 7	-	11	35	mA



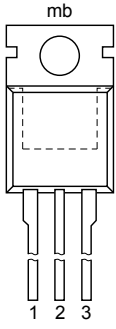
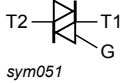
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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G+; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	-	23	70	mA

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 <p>TO-220AB (SOT78)</p>	
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2		

6. Ordering information

Table 3. Ordering information

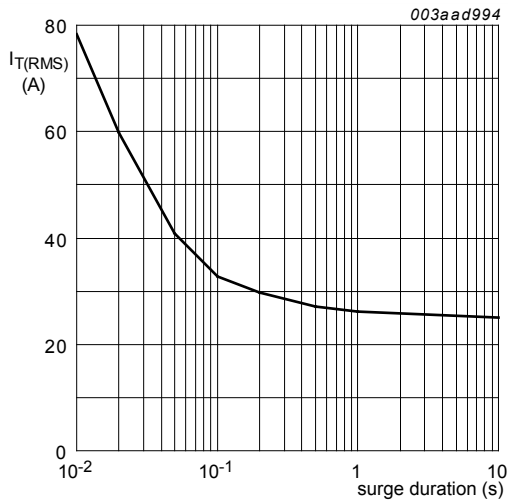
Type number	Package		
	Name	Description	Version
BTA140-800	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 91\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	25	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	190	A
		full sine wave; $T_{j(\text{init})} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$	-	209	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; SIN	-	180	A^2s
di_T/dt	rate of rise of on-state current	$I_T = 30\text{ A}$; $I_G = 0.2\text{ A}$; $dI_G/dt = 0.2\text{ A}/\mu s$; T2+ G+	-	50	$A/\mu s$
		$I_T = 30\text{ A}$; $I_G = 0.2\text{ A}$; $dI_G/dt = 0.2\text{ A}/\mu s$; T2+ G-	-	50	$A/\mu s$
		$I_T = 30\text{ A}$; $I_G = 0.2\text{ A}$; $dI_G/dt = 0.2\text{ A}/\mu s$; T2- G-	-	50	$A/\mu s$
		$I_T = 30\text{ A}$; $I_G = 0.2\text{ A}$; $dI_G/dt = 0.2\text{ A}/\mu s$; T2- G+	-	10	$A/\mu s$
I_{GM}	peak gate current		-	2	A
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T_{stg}	storage temperature		-40	150	$^{\circ}C$
T_j	junction temperature		-	125	$^{\circ}C$



f = 50 Hz; T_{mb} = 91 °C

Fig. 1. RMS on-state current as a function of surge duration; maximum values

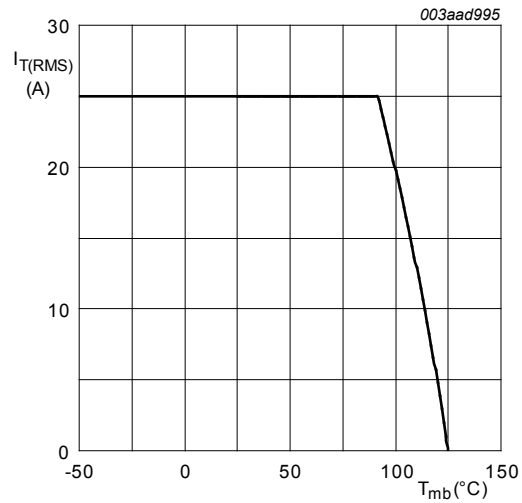
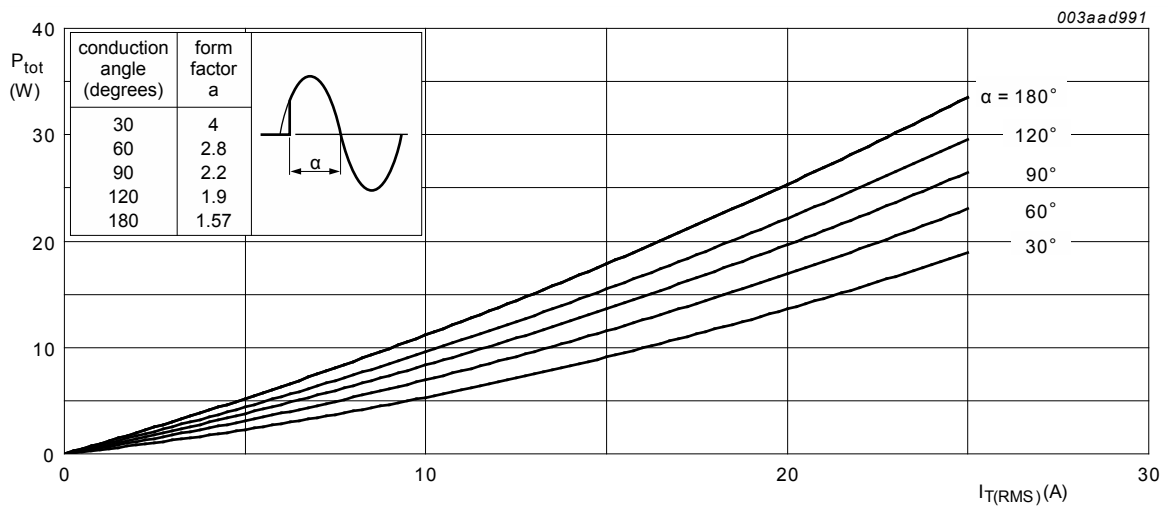


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values



α = conduction angle
 a = form factor = $I_{T(RMS)} / I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

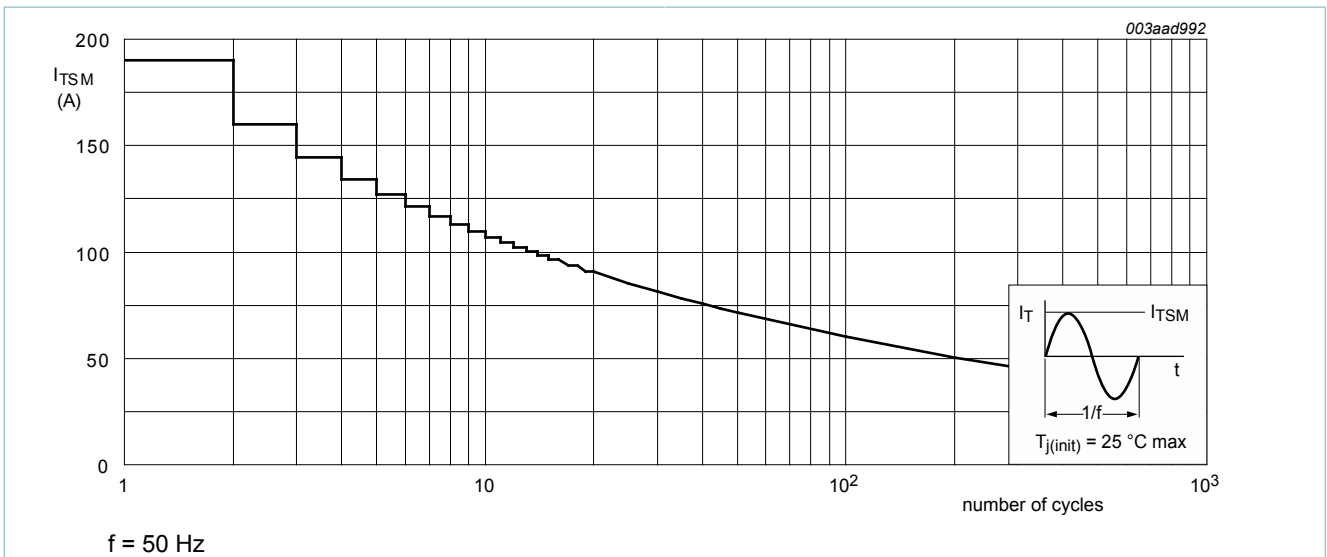


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

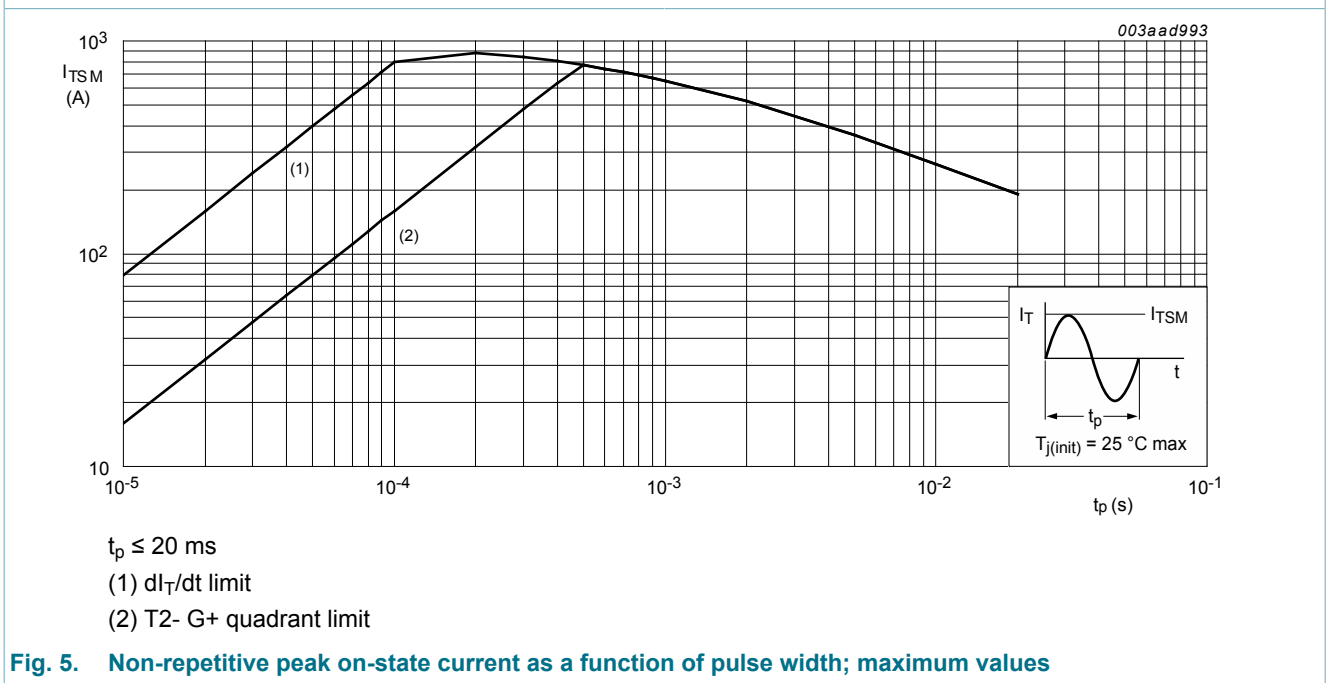
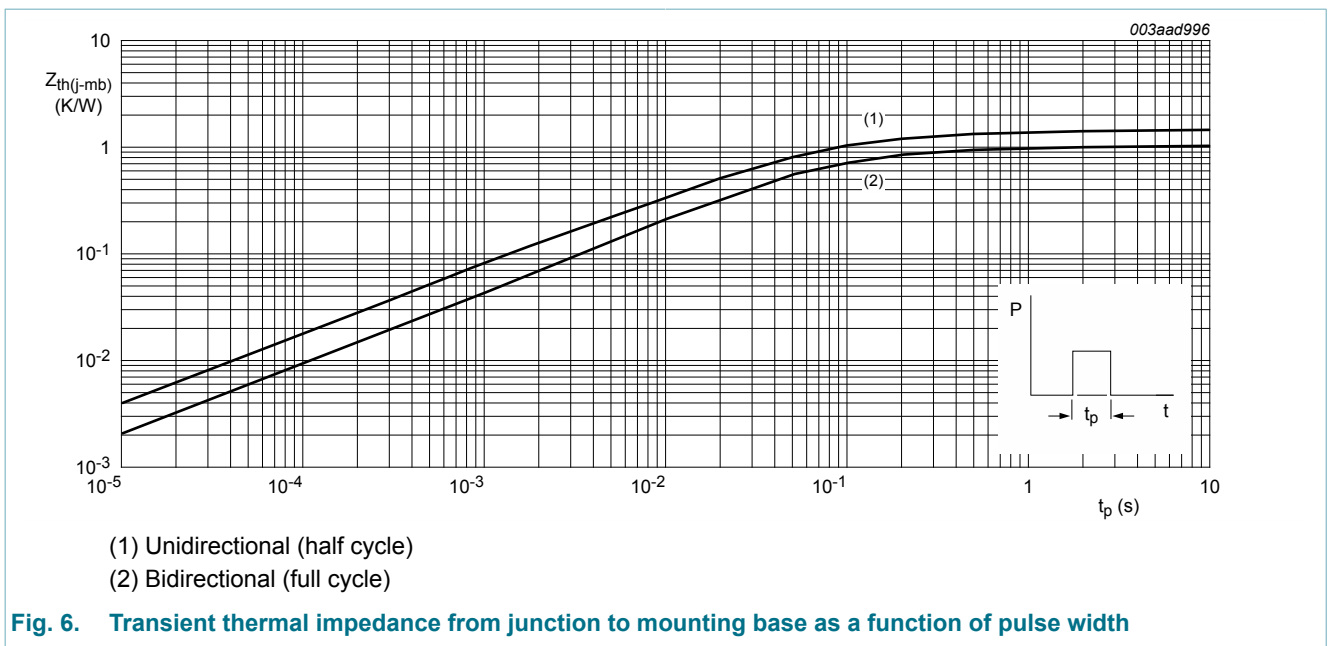


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

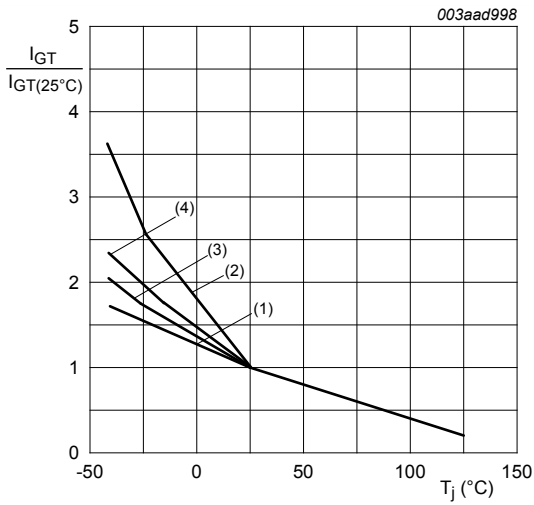
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; Fig. 6	-	-	1	K/W
		half cycle; Fig. 6	-	-	1.4	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W



9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 7	-	6	35	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 7	-	10	35	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; Fig. 7	-	11	35	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; Fig. 7	-	23	70	mA
I _L	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; Fig. 8	-	8	40	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; Fig. 8	-	13	60	mA
		V _D = 12 V; I _G = 0.1 A; T2- G-; T _j = 25 °C; Fig. 8	-	18	40	mA
		V _D = 12 V; I _G = 0.1 A; T2- G+; T _j = 25 °C; Fig. 8	-	15	60	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; T2+; Fig. 9	-	7	60	mA
		V _D = 12 V; T _j = 25 °C; T2-; Fig. 9	-	12	60	mA
V _T	on-state voltage	I _T = 30 A; T _j = 25 °C; Fig. 10	-	1.3	1.55	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic characteristics						
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 536 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	100	300	-	V/μs
dV _{com} /dt	rate of change of commutating voltage	V _D = 400 V; T _j = 95 °C; dI _{com} /dt = 9 A/ms; I _T = 25 A; gate open circuit	-	10	-	V/μs
t _{gt}	gate-controlled turn-on time	I _{TM} = 30 A; V _D = 800 V; I _G = 0.1 A; dI _G /dt = 5 A/μs	-	2	-	μs



- (1) T2+ G+
- (2) T2+ G-
- (3) T2- G-
- (4) T2- G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

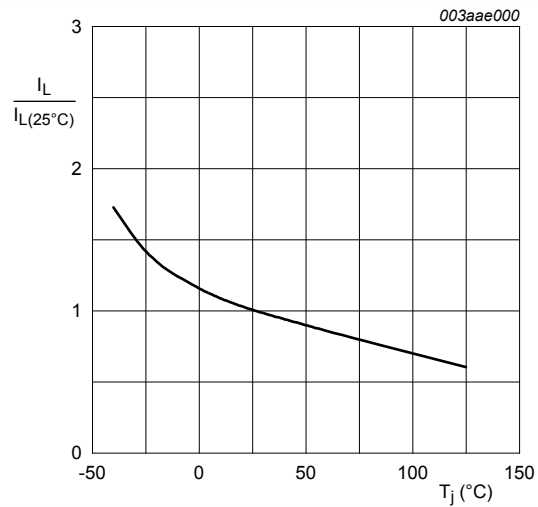


Fig. 8. Normalized latching current as a function of junction temperature

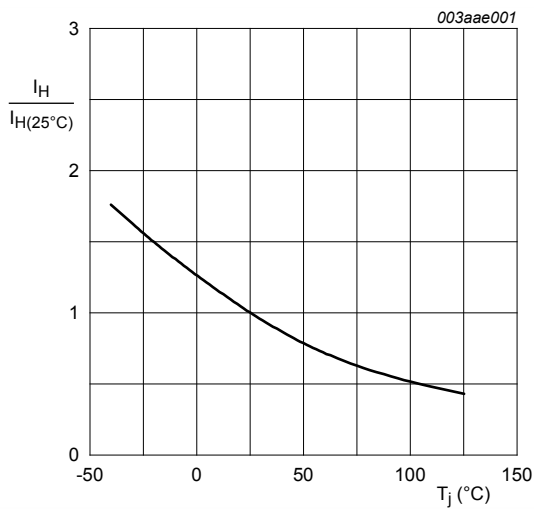
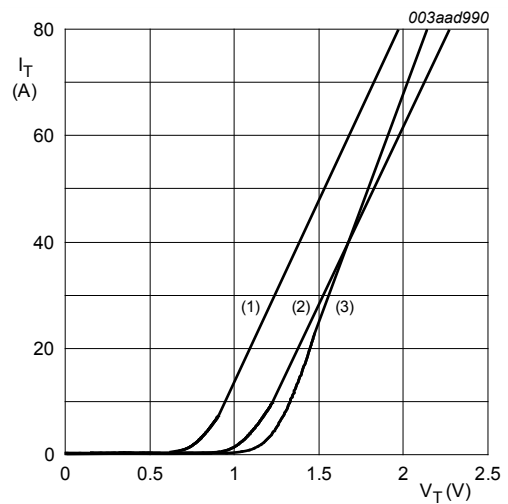


Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 1.073 \text{ V}; R_s = 0.015 \Omega$

- (1) $T_j = 125^\circ\text{C}$; typical values
- (2) $T_j = 125^\circ\text{C}$; maximum values
- (3) $T_j = 25^\circ\text{C}$; maximum values

Fig. 10. On-state current as a function of on-state voltage

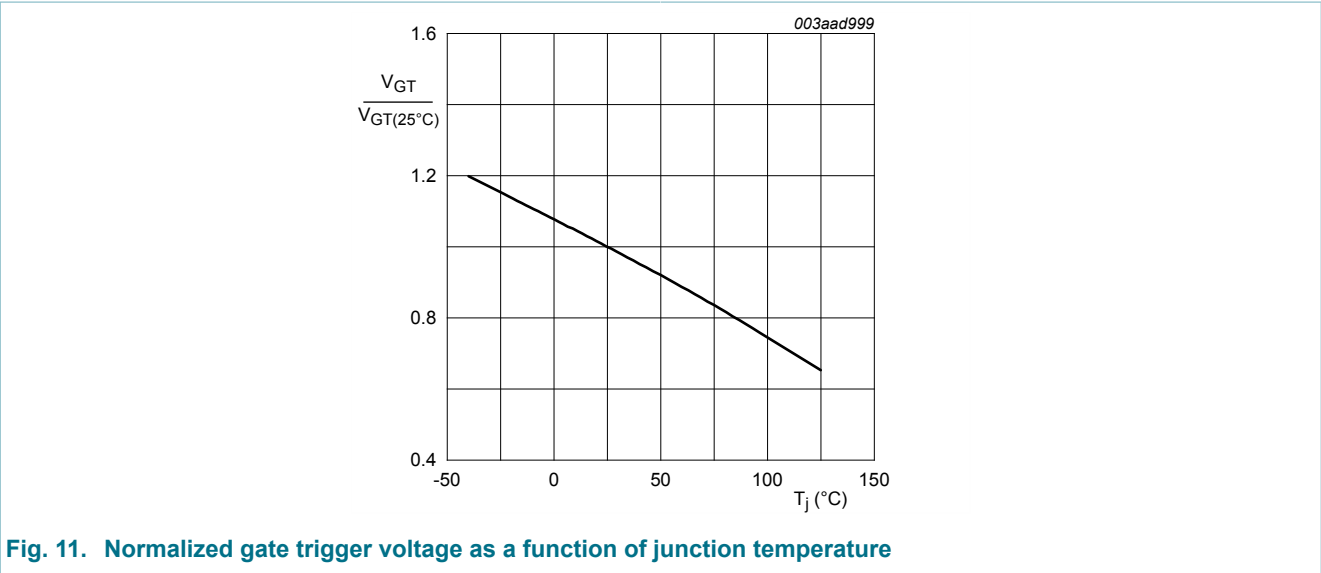


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

10. Package outline

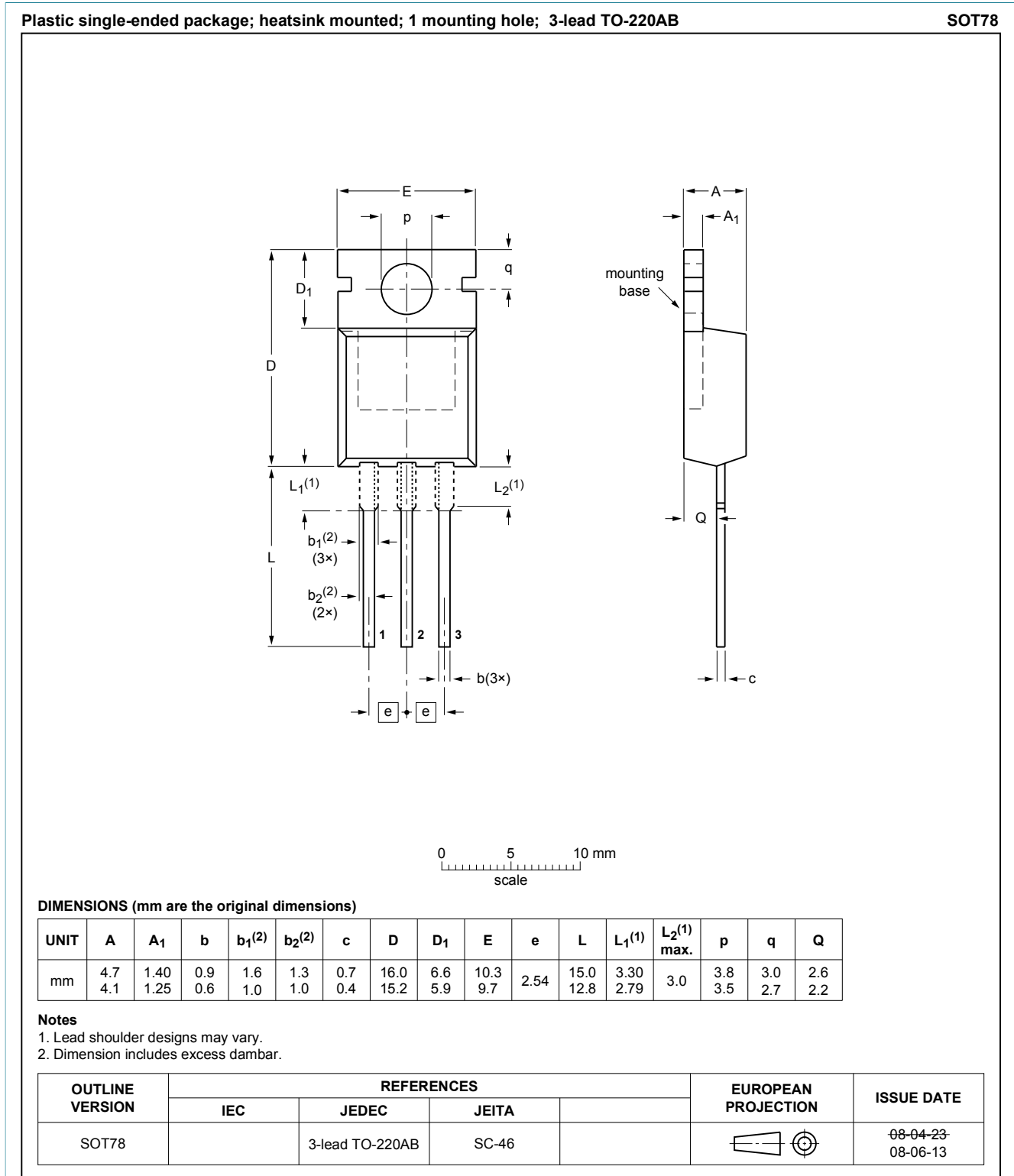


Fig. 12. Package outline TO-220AB (SOT78)

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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